ALPHA & OMEGA SEMICONDUCTOR

AO4824
Asymmetric Dual N-Channel Enhancement Mode Field Effect Transistor

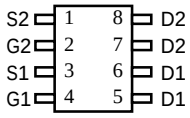
General Description

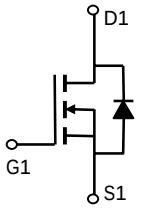
The AO4824 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The two MOSFETs make a compact and efficient switch and synchronous rectifier combination for use in DC-DC converters. *Standard Product AO4824 is Pb-free (meets ROHS & Sony 259 specifications). AO4824L is a Green Product ordering option. AO4824 and AO4824L are electrically identical.*

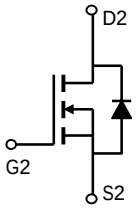
Features

Q1	Q2	
V_{DS} (V) = 30V	V_{DS}(V) = 30V	
I_D = 8.5A	I_D=9.8A	(V_{GS} = 10V)
$R_{DS(ON)}$ < 17mΩ	<13mΩ	(V_{GS} = 10V)
$R_{DS(ON)}$ < 27mΩ	<15mΩ	(V_{GS} = 4.5V)

SOIC-8







Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Max Q1	Max Q2	Units
Drain-Source Voltage		V_{DS}	30	30	V
Gate-Source Voltage		V_{GS}	±20	±12	V
Continuous Drain Current [A]	T_A=25°C	I_D	8.5	9.8	A
	T_A=70°C		6.8	7.8	
Pulsed Drain Current [B]		I_{DM}	30	40	
Power Dissipation	T_A=25°C	P_D	2	2	W
	T_A=70°C		1.28	1.28	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	-55 to 150	°C

Parameter: Thermal Characteristics MOSFET Q1		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	48	62.5	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		74	110	
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$	35	40	

Parameter: Thermal Characteristics MOSFET Q2		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	48	62.5	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		74	110	
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$	35	40	

Q1 Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V		30			V
I_{DSS}	Zero Gate Voltage Drain Current	I_D=250µA, V_{GS}=0V			0.003	1	
		V_{DS}=24V, V_{GS}=0V	T_J=55°C			5	µA
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±20V				100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250µA		1	1.8	3	V
$I_{D(ON)}$	On state drain current	V_{GS}=10V, V_{DS}=5V		30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=8.5A			13.8	17	mΩ
			T_J=125°C		20	25	mΩ
g_{FS}		V_{GS}=4.5V, I_D=6A			21	27	mΩ
V_{SD}	Forward Transconductance	V_{DS}=5V, I_D=8.5A			23		S
I_S	Diode Forward Voltage	I_S=1A,V_{GS}=0V			0.76	1	V
	Maximum Body-Diode Continuous Current					3	A
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz			1040	1250	pF
C_{oss}	Output Capacitance				180		pF
C_{rss}	Reverse Transfer Capacitance				110		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz			0.7	0.85	Ω
SWITCHING PARAMETERS							
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=15V, I_D=8.5A			19.2	23	nC
Q_g(4.5V)	Total Gate Charge				9.36	11.2	nC
Q_{gs}	Gate Source Charge				2.6		nC
Q_{gd}	Gate Drain Charge				4.2		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=1.8Ω, R_{GEN}=3Ω			5.2	7.5	ns
t_r	Turn-On Rise Time				4.4	6.5	ns
$t_{D(off)}$	Turn-Off DelayTime				17.3	25	ns
t_f	Turn-Off Fall Time				3.3	5	ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=8.5A, dI/dt=100A/µs			16.7	21	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=8.5A, dI/dt=100A/µs			6.7	10	nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t≤ 10s thermal resistance rating.
B: Repetitive rating, pulse width limited by junction temperature.
C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.
D. The static characteristics in Figures 1 to 6 are obtained using 80µs pulses, duty cycle 0.5% max.
E. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.
Rev 4 : Aug 2005

Q1 TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

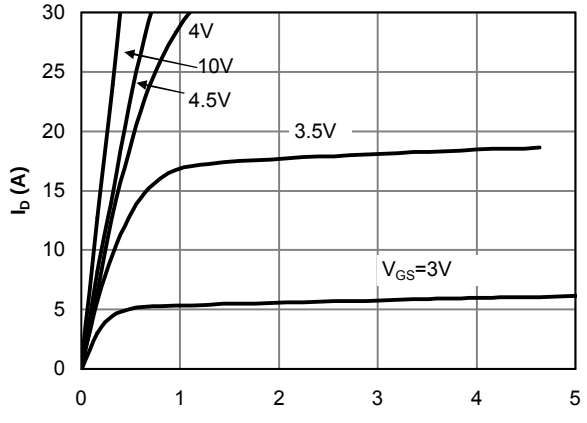


Fig 1: On-Region Characteristics

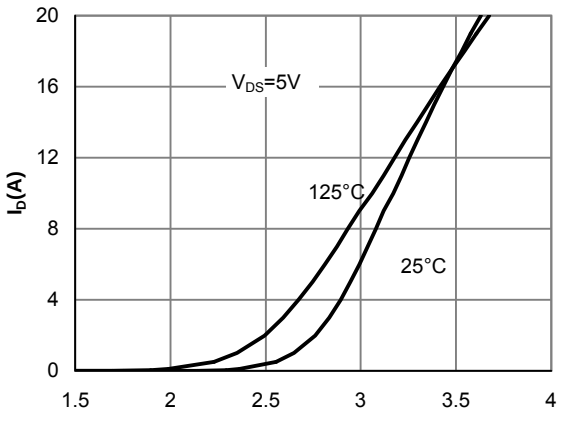


Figure 2: Transfer Characteristics

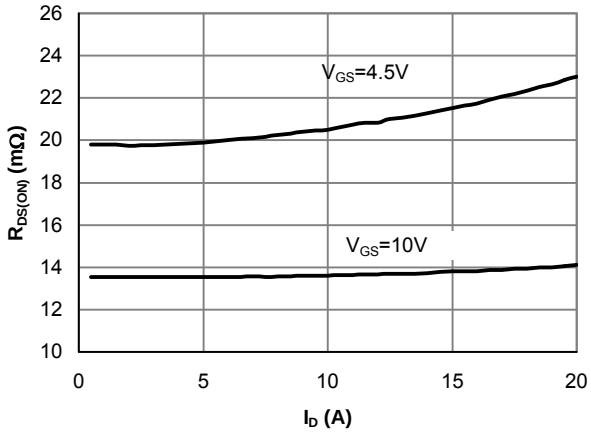


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

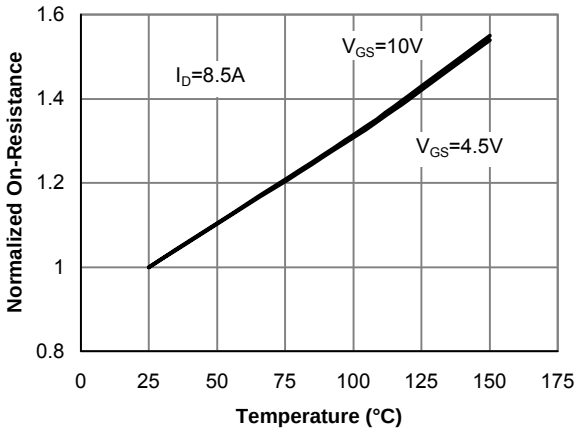


Figure 4: On-Resistance vs. Junction Temperature

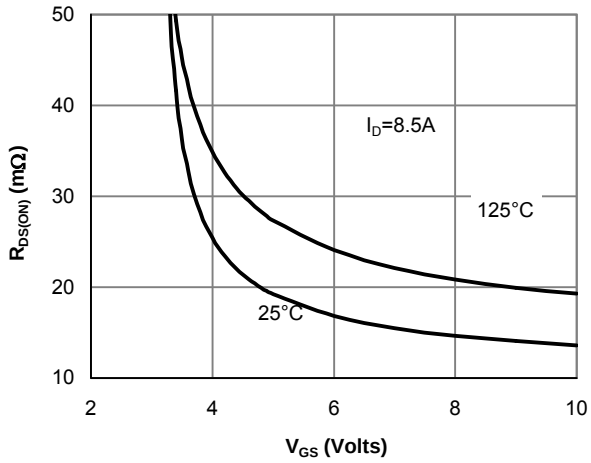


Figure 5: On-Resistance vs. Gate-Source Voltage

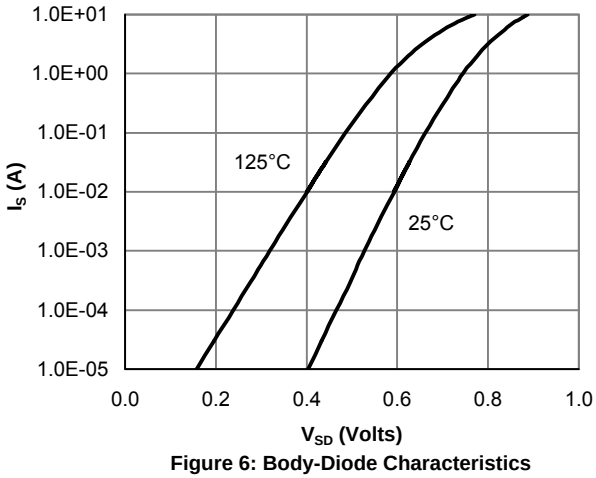


Figure 6: Body-Diode Characteristics

Q1 TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

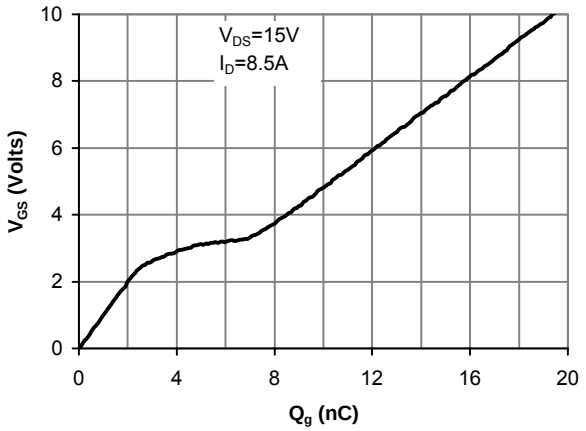


Figure 7: Gate-Charge Characteristics

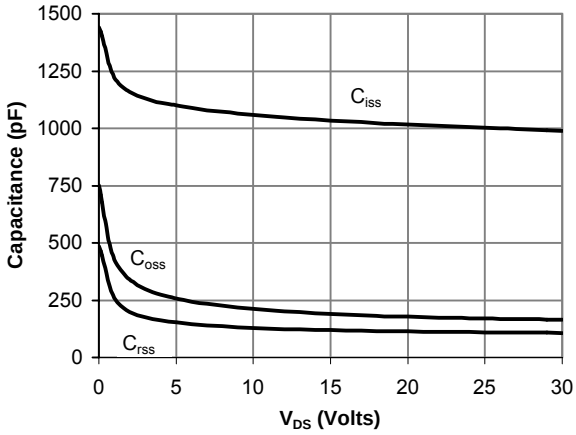


Figure 8: Capacitance Characteristics

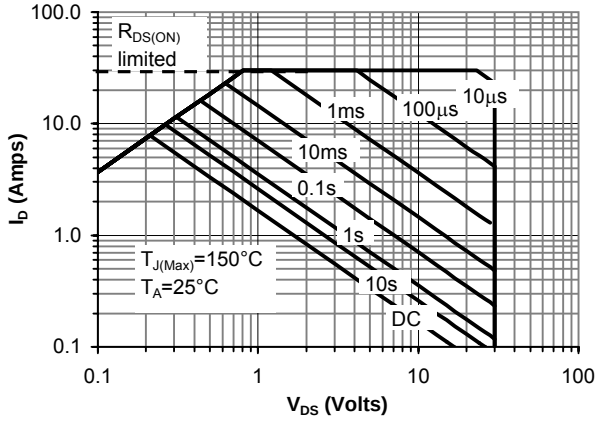


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

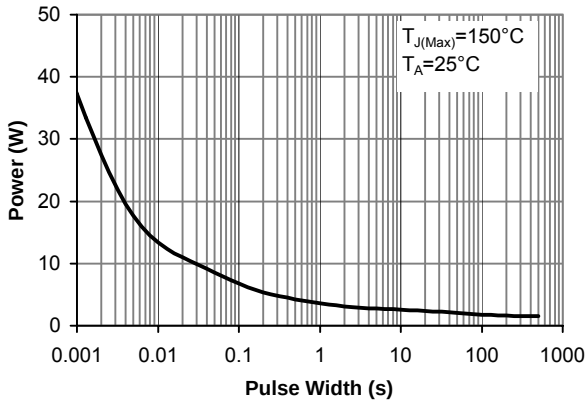


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

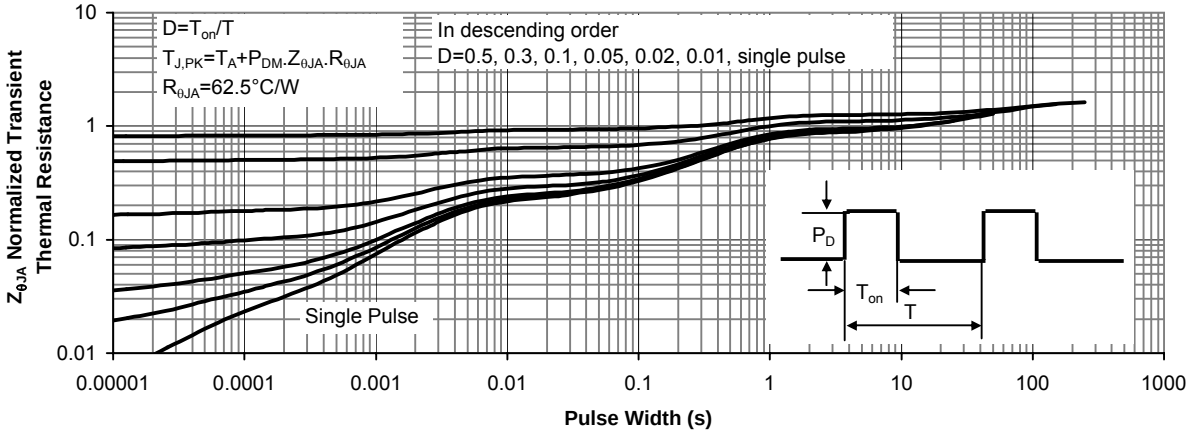


Figure 11: Normalized Maximum Transient Thermal Impedance

Q2 Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=24V, V_{GS}=0V		0.004	1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±12V			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250µA	0.6	1.1	2	V
$I_{D(ON)}$	On state drain current	V_{GS}=4.5V, V_{DS}=5V	40			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=9.8A		10.5	13	mΩ
		T_J=125°C		13.4	17	
		V_{GS}=4.5V, I_D=9A		12	15	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=9.8A	30	37		S
V_{SD}	Diode Forward Voltage	I_S=1A		0.73	1	V
I_S	Maximum Body-Diode Continuous Current				3	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz		3656	4250	pF
C_{oss}	Output Capacitance			256		pF
C_{rss}	Reverse Transfer Capacitance			168		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		0.86	1.05	Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=4.5V, V_{DS}=15V, I_D=9.8A		30.5	36	nC
Q_{gs}	Gate Source Charge			4.5		nC
Q_{gd}	Gate Drain Charge			8.5		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=1.6Ω, R_{GEN}=3Ω		5.5	8.2	ns
t_r	Turn-On Rise Time			3.1	5	ns
$t_{D(off)}$	Turn-Off DelayTime			52.4	75	ns
t_f	Turn-Off Fall Time			5.7	8.5	ns
t_{rr}	Body Diode Reverse Recovery time	I_F=9.8A, dI/dt=100A/µs		21.5	26	ns
Q_{rr}	Body Diode Reverse Recovery charge	I_F=9.8A, dI/dt=100A/µs		11	15	nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80µs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

Rev 4: Aug 2005

Q2 TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

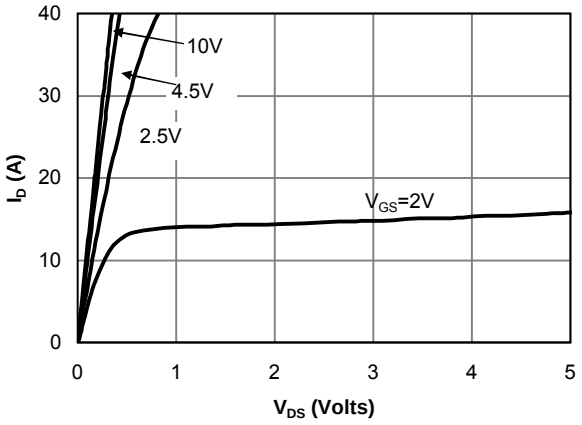


Fig 1: On-Region Characteristics

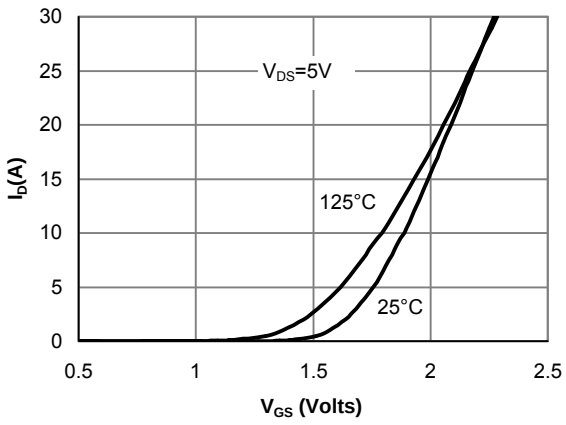
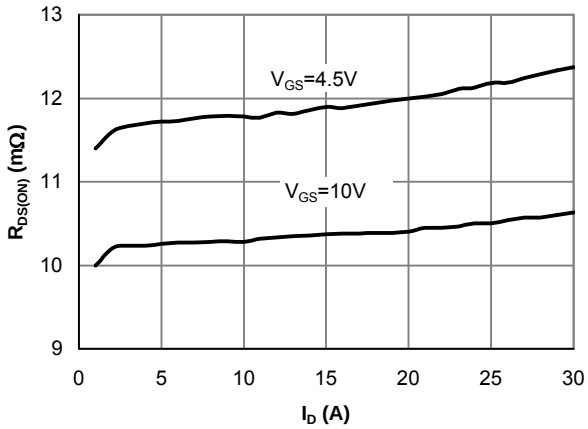


Figure 2: Transfer Characteristics



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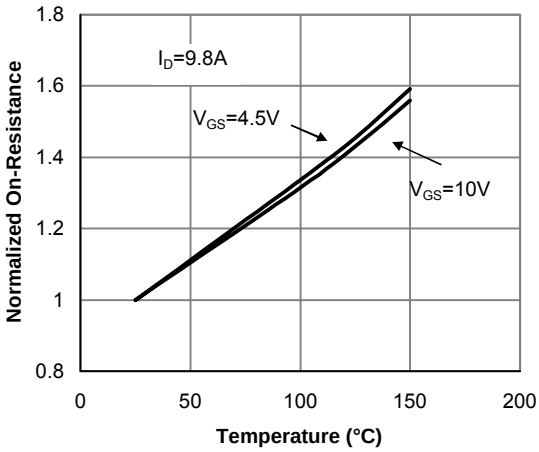
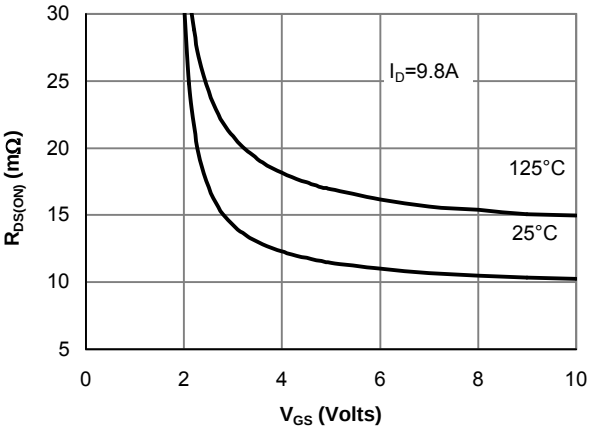


Figure 4: On resistance vs. Junction Temperature



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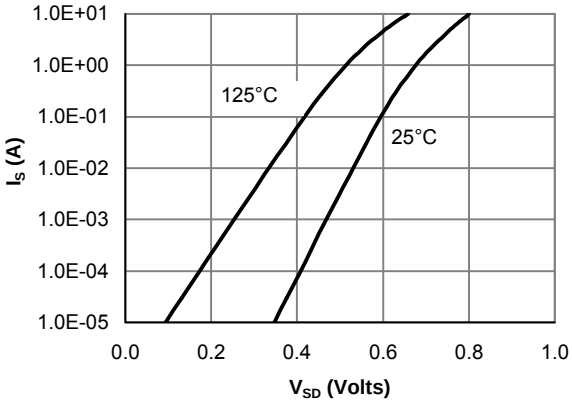

Figure 6: Body-Diode Characteristics

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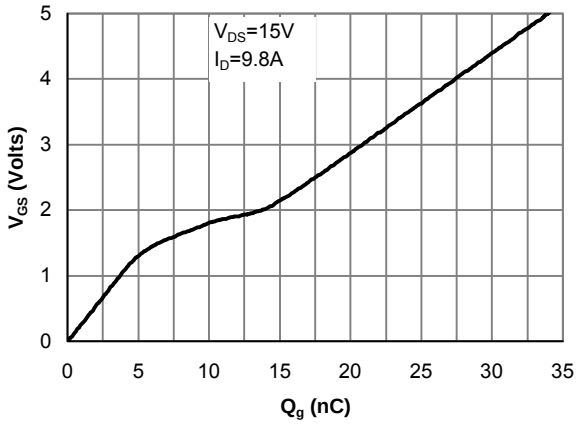

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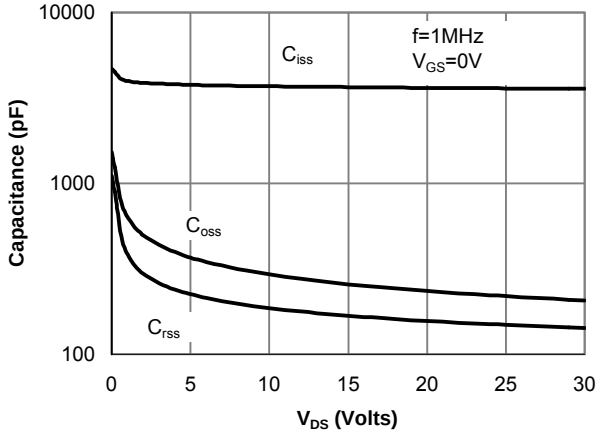

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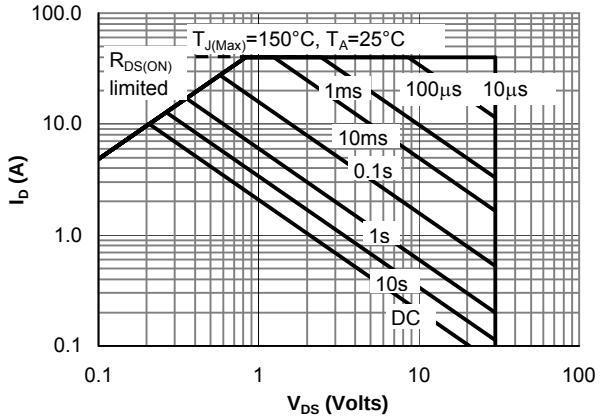

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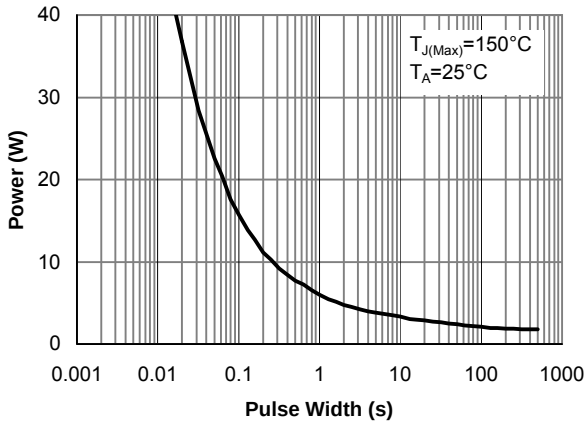

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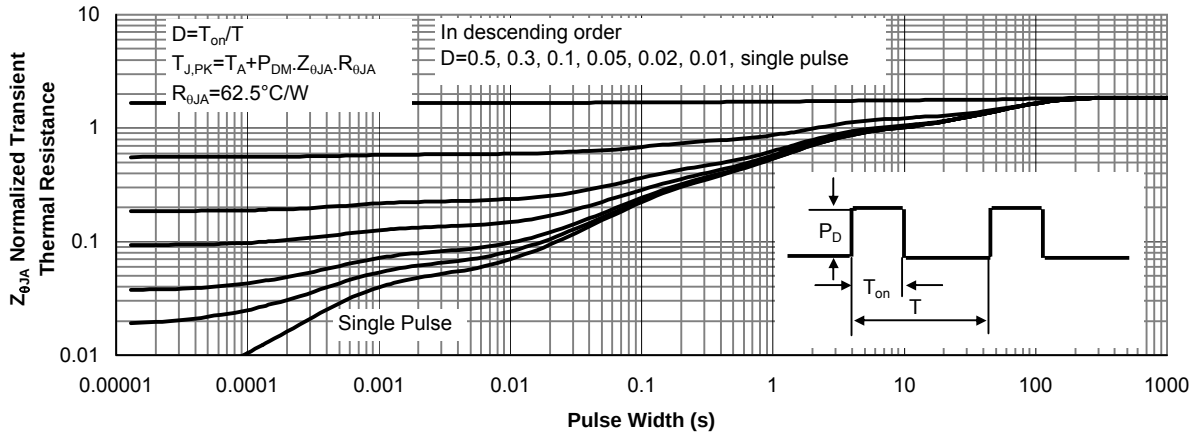

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